

2200nm InGaAs 1000um PD Chip datasheet

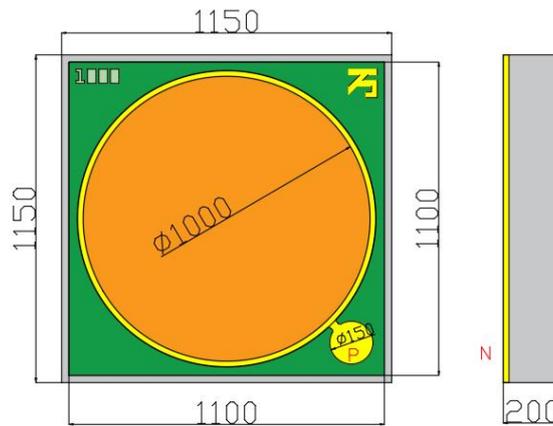
P/N : WIR4-1000

Application

Optical sensor
 Gas sensor for CO₂
 Optical power meter
 900-2200nm Spectral range

Structure

InGaAs / InP PIN Chip.
 P Electrode (anode) : Gold.
 N Electrode (cathode) : Gold.



DIMENSIONS

Conditions	Min.	Typ.	Max	Unit
Active	995	1000	1005	μm
Chip width	1130	1150	1170	μm
Chip length	1130	1150	1170	μm
Chip height	180	200	220	μm
Pad Area	140	150	160	μm

Electro-Optical Characteristics (@ Ta=25 °C)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Dark current	Id	Vr=-0.5V		900	1000	nA
Responsivity	R	Vr=0V,@2000 nm	1.0	1.2	-	A/W
Capacitance	Cp	Vr=0V, f=1MHz		440	1000	pF
Wavelength range	λ		900	2004	2200	nm

ABSOLUTE MAXIMUM RATING

Parameter	Rating
Operating Temperature	-40°C to 85°C
Storage Temperature	-55°C to 125°C
Forward Current	10mA